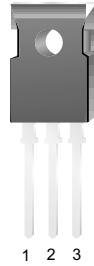




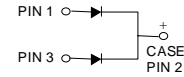
# MBR3035PT - MBR3060PT

## Features

- Low power loss, high efficiency.
- High surge capacity.
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.
- Metal silicon junction, majority carrier conduction.
- High current capacity, low forward voltage drop.
- Guard ring for over voltage protection.



TO-3P/TO-247AD



## Schottky Rectifiers

### Absolute Maximum Ratings\*

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value				Units
		3035PT	3045PT	3050PT	3060PT	
$V_{RRM}$	Maximum Repetitive Reverse Voltage	35	45	50	60	V
$I_{F(AV)}$	Average Rectified Forward Current	30				A
$I_{FSM}$	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	200				A
$T_{stg}$	Storage Temperature Range	-65 to +175				$^\circ\text{C}$
$T_J$	Operating Junction Temperature	-65 to +150				$^\circ\text{C}$

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Power Dissipation	3.0	W
$R_{\theta JL}$	Thermal Resistance, Junction to Lead	1.4	$^\circ\text{C}/\text{W}$

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Device				Units
		3035PT	3045PT	3050PT	3060PT	
$V_F$	Forward Voltage $I_F = 20\text{ A}, T_C = 25^\circ\text{C}$	-		0.75		V
	$I_F = 20\text{ A}, T_C = 125^\circ\text{C}$	0.60		0.65		V
	$I_F = 30\text{ A}, T_C = 25^\circ\text{C}$	0.76		-		V
	$I_F = 30\text{ A}, T_C = 125^\circ\text{C}$	0.72		-		V
$I_R$	Reverse Current @ rated $V_R$ $T_A = 25^\circ\text{C}$	1.0		5.0		mA
	$T_A = 125^\circ\text{C}$	60		100		mA
$I_{RRM}$	Peak Repetitive Reverse Surge Current 2.0 us Pulsu Width, $f = 1.0\text{ KHz}$	1.0		0.5		A

MBR3035PT - MBR3060PT

Typical Characteristics

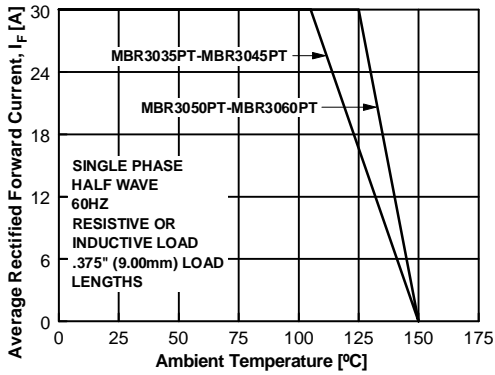


Figure 1. Forward Current Derating Curve

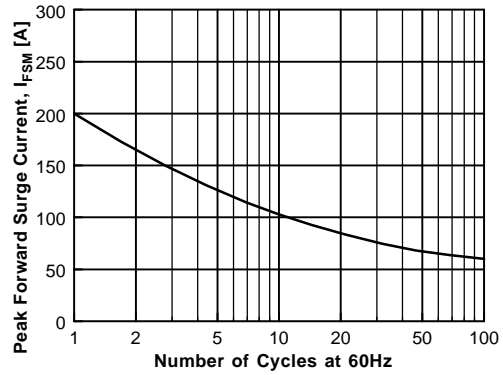


Figure 2. Non-Repetitive Surge Current

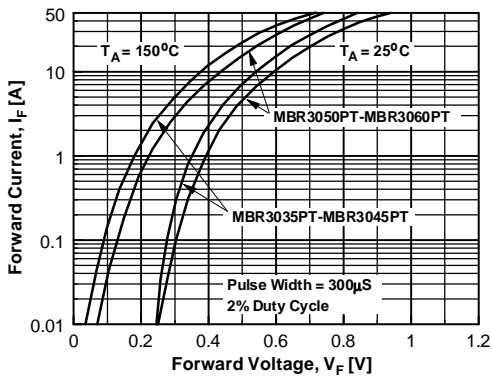


Figure 3. Forward Voltage Characteristics

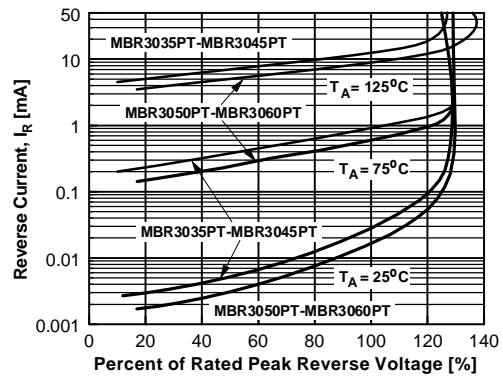


Figure 4. Reverse Current vs Reverse Voltage

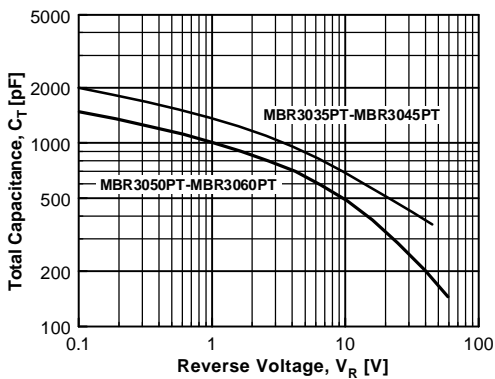


Figure 5. Total Capacitance

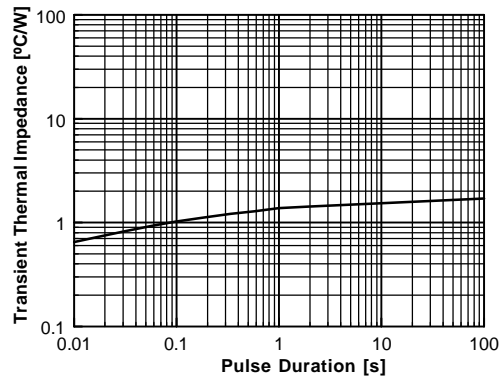


Figure 6. Thermal Impedance Characteristics

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE <sub>x</sub> <sup>TM</sup>	FAST <sup>®</sup>	OPTOLOGIC <sup>TM</sup>	SMART START <sup>TM</sup>	VCX <sup>TM</sup>
Bottomless <sup>TM</sup>	FAST <sub>r</sub> <sup>TM</sup>	OPTOPLANAR <sup>TM</sup>	STAR*POWER <sup>TM</sup>	
CoolFET <sup>TM</sup>	FRFET <sup>TM</sup>	PACMAN <sup>TM</sup>	Stealth <sup>TM</sup>	
CROSSVOLT <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	POPT <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
DenseTrench <sup>TM</sup>	GTO <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
DOMET <sup>TM</sup>	HiSeC <sup>TM</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>TM</sup> -8	
EcoSPARK <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	QFET <sup>TM</sup>	SyncFET <sup>TM</sup>	
E <sup>2</sup> CMOS <sup>TM</sup>	LittleFET <sup>TM</sup>	QST <sup>TM</sup>	TinyLogic <sup>TM</sup>	
EnSigna <sup>TM</sup>	MicroFET <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	TruTranslation <sup>TM</sup>	
FACT <sup>TM</sup>	MicroPak <sup>TM</sup>	Quiet Series <sup>TM</sup>	UHC <sup>TM</sup>	
FACT Quiet Series <sup>TM</sup>	MICROWIRE <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	UltraFET <sup>®</sup>	

STAR\*POWER is used under license

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.